L Number	Hits	Search Text	DB	Time stamp
-	19031	(cmp or polish or polishing or planarize or planarizing) and test	USPAT.	2003/09/24
-	1653	(cmp or polish or polishing or planarize or planarizing).ab. and test	USPAT	2003/09/12
_	205	((cmp or polish or polishing or planarize or planarizing).ab. and test) and (trench or STI)	USPAT	15:38 2003/09/12 15:39
_	1	(((cmp or polish or polishing or planarize or planarizing).ab. and test) and (trench or STI)) and (reclaim or reclaiming)	USPAT	2003/09/12 15:39
_	193		USPAT	2003/09/12 15:42
	189	<pre>((((cmp or polish or polishing or planarize or planarizing).ab. and test) and (trench or STI)) and semiconductor) and @ay<=2001</pre>	USPAT	2003/09/15 11:31
_	3681	(cmp or polish or polishing or planarize or planarizing).ab. and pattern	USPAT	2003/09/15
_	1169	((cmp or polish or polishing or planarize or planarizing).ab. and pattern) and (trench or STI)	USPAT	2003/09/15 11:36
_	922	(((cmp or polish or polishing or planarize or planarizing).ab. and pattern) and (trench or STI)) and ((silicon adj oxide) or SiO or SiO?sub.2 or (silicon adj dioxide))	USPAT	2003/09/15 15:25
-	127	(((cmp or polish or polishing or planarize or planarizing).ab. and pattern) and (trench or STI)) and ((silicon adj oxide) or SiO or SiO?sub.2 or (silicon adj dioxide))) and sacrificial	USPAT	2003/09/15 11:58
_	1992	<pre>((cmp or polish or polishing or planarize or planarizing).ab. and pattern) and ((silicon adj oxide) or SiO or SiO?sub.2 or (silicon adj dioxide))</pre>	USPAT	2003/09/15 11:58
-	196	(((cmp or polish or polishing or planarize or planarizing).ab. and pattern) and ((silicon adj oxide) or SiO or SiO?sub.2 or (silicon adj dioxide))) and sacrificial	USPAT	2003/09/15 12:02
_	178	<pre>((((cmp or polish or polishing or planarize or planarizing).ab. and pattern) and ((silicon adj oxide) or SiO or SiO?sub.2 or (silicon adj dioxide))) and sacrificial) and @ay<=2000</pre>	USPAT	2003/09/15 12:02
_	18	((cmp or polish or polishing or planarize or planarizing).ab. and pattern) and (reclaim or reclaimed or reclaimation)	USPAT	2003/09/15 13:31
_	498	(cmp or polish or polishing or planarize or planarizing) and (reclaim or reclaiming or reclaimed or reclaimation)	USPAT	2003/09/15 13:33
_	88	((cmp or polish or polishing or planarize or planarizing) and (reclaim or reclaiming or reclaimed or reclaimation)) and ((silicon adj oxide) or SiO or	USPAT	2003/09/15 13:39
_	81	SiO?sub.2 or (silicon adj dioxide)) (((cmp or polish or polishing or planarize or planarizing) and (reclaim or reclaiming or reclaimed or reclaimation)) and ((silicon adj oxide) or SiO or SiO?sub.2 or (silicon adj dioxide))) and	USPAT	2003/09/15 13:39
_	86	<pre>@ay<=2000 (cmp or polish or polishing or planarize or planarizing).ab. and (test with pattern)</pre>	USPAT	2003/09/15 13:54

		•		
_	85	<pre>((cmp or polish or polishing or planarize or planarizing).ab. and (test with pattern)) not (((cmp or polish or</pre>	USPAT	2003/09/15 13:54
		polishing or planarize or planarizing) and (reclaim or reclaiming or reclaimed or reclaimation)) and ((silicon adj		
		oxide) or SiO or SiO?sub.2 or (silicon adj dioxide))) and @ay<=2000)		
_	74	(((cmp or polish or polishing or planarize or planarizing).ab. and (test with pattern)) not (((cmp or polish or	USPAT	2003/09/15 14:03
		polishing or planarize or planarizing) and (reclaim or reclaiming or reclaimed or reclaimation)) and ((silicon adjoxide) or SiO or SiO?sub.2 or (silicon		
_	6	adj dioxide))) and @ay<=2000)) and @ay<=2000 Lacy-Michael-S.in.	USPAT	2003/09/15
	56	("3753269" "4318250" "4510113"		14:03
	36	"4576612" "4672985" "4720939" "4728552" "4753838" "4841680" "4927432" "4934102" "4954141" "4962562" "5020283" "5081051"	USPAT	2003/09/15
		"5104421" "5177908" "5197999" "5212910" "5234867" "5257478" "5287663" "5329734" "5335453" "5433651" "5484323" "5487697"		
		"5489233" "5531635" "5534106" "5536202" "5547417" "5558568" "5575707" "5578362" "5593344" "5605760" "5611943" "5622526"	,	
		"5643044" "5655951" "5692947" "5692950" "5725417" "5759918" "5762536" "5779526" "5810964" "5871390" "5897426" "5899798" "5908530" "5958794" "6093651"		
_	2821	"6106351" "6206759").PN. (cmp or polish or polishing or planarize or planarizing) and sacrificial	USPAT	2003/09/15
_	1700	((cmp or polish or polishing or planarize or planarizing) and sacrificial) and ((strip or stripping or remove or	USPAT	15:07 2003/09/15 15:09
	400	removing or etch or etching) with sacrificial)	`	
	402	((cmp or polish or polishing or planarize or planarizing) and sacrificial) and ((strip or stripping or remove or removing or etch or etching) with	USPAT	2003/09/15
_	345	(sacrificial near oxide)) (((cmp or polish or polishing or planarize or planarizing) and sacrificial) and ((strip or stripping or remove or removing or etch or etching)	USPAT	2003/09/15 15:11
_	22	with (sacrificial near oxide))) and @ay<=2000 ((((cmp or polish or polishing or planarize or planarizing) and	USPAT	2003/09/15 15:10
	-	<pre>sacrificial) and ((strip or stripping or remove or removing or etch or etching) with (sacrificial near oxide))) and @ay<=2000) and (test or testing)</pre>		
_	182	((((cmp or polish or polishing or planarize or planarizing) and sacrificial) and ((strip or stripping or remove or removing or etch or etching) with (sacrificial near oxide))) and @ay<=2000) and ((trench or STI) same	USPAT	2003/09/15 15:24
_	664	sacrificial) (re\$1claim or re\$1claiming or re\$1claimed	USPAT	2003/09/15
	1004	or reclaimation) and semiconductor	OSPAI	2003/09/15 15:25

r		777012-1-01		.,
_	157	((re\$1claim or re\$1claiming or re\$1claimed or reclaimation) and	USPAT	2003/09/15 15:26
		semiconductor) and ((silicon adj oxide) or SiO or SiO?sub.2 or (silicon adj		
		dioxide) or sacrificial)		
_	147	(((re\$1claim or re\$1claiming or re\$1claimed or reclaimation) and	USPAT	2003/09/15
		semiconductor) and ((silicon adj oxide)		15:26
		or SiO or SiO?sub.2 or (silicon adj		
	499	dioxide) or sacrificial)) and @ay<=2000	TIGDAM.	2002/00/16
-	499	(CMP or polishing or polish or planarize or planarizing) and (reclaim or	USPAT	2003/09/16
		reclaiming or reclaimed or reclaimation)		10.52
-	472	((CMP or polishing or polish or planarize	USPAT	2003/09/16
		or planarizing) and (reclaim or reclaiming or reclaimed or reclaimation))		16:33
		and @ay<=2000		
-	111	· · ·	USPAT	2003/09/16
		planarize or planarizing) and (reclaim or reclaiming or reclaimed or reclaimation))		16:34
		and @ay<=2000) and semiconductor		
	7	("3923567" "4738056" "5051375"	USPAT	2003/09/16
		"5131979" "5622875" "5855735" "5981301").PN.		16:34
-	121	(reclaim or reclaiming or reclaimed or	USPAT	2003/09/20
		reclaimation) and (trench or STI)		10:41
-	20	5622875.URPN.	USPAT	2003/09/20
_	7	("3923567" "4738056" "5051375"	USPAT	2003/09/20
		"5131979" "5622875" "5855735"		10:47
_	11	"5981301").PN. 5131979.URPN.	HCDAE	2002/00/20
		3131979. ORPN.	USPAT	2003/09/20
-	921	(cmp or polish or polishing or planarize	USPAT	2003/09/24
		or planarizing) and (test near3 (pattern or structure))		11:30
_	591	((cmp or polish or polishing or planarize	USPAT	2003/09/24
		or planarizing) and (test near3 (pattern		11:27
		or structure))) and (oxide or dioxide or SiO or SiO?sub.2)		
-	591	(((cmp or polish or polishing or	USPAT	2003/09/24
		planarize or planarizing) and (test near3		11:29
		(pattern or structure))) and (oxide or dioxide or SiO or SiO?sub.2)) and (cmp		
		or polish or polishing or planarize or		
	F 4 P	planarizing or planarization)		0000/65/5
_	517	<pre>((((cmp or polish or polishing or planarize or planarizing) and (test near3</pre>	USPAT	2003/09/24
		(pattern or structure))) and (oxide or		11.43
		dioxide or SiO or SiO?sub.2)) and (cmp		
		or polish or polishing or planarize or planarizing or planarization)) and		
		(silicon or semiconductor)		
-	87	(((((cmp or polish or polishing or	USPAT	2003/09/24
		planarize or planarizing) and (test near3 (pattern or structure))) and (oxide or		13:17
		dioxide or SiO or SiO?sub.2)) and (cmp		
		or polish or polishing or planarize or		
		<pre>planarizing or planarization)) and (silicon or semiconductor)) and ((cmp or</pre>		,
		polish or polishing or planarize or		
		<pre>planarizing) same(test near3 (pattern or structure)))</pre>	-	
_	15	("5278105" "5386088" "5652465"	USPAT	2003/09/24
		"5665633" "5747380" "5885856"		11:31
		"5923563" "5948573" "5956618" "5970238" "6087733" "6232161"		
		"5970238" "6087733" "6232161" "6281049" "6448630" "6486066").PN.		
-	6	("5736427" "6136709" "6214716"	USPAT	2003/09/24
		"6274483" "6297156" "6306737").PN.		11:41

_	3821	(sacrifice or sacrificial) with (oxide or	USPAT	2003/09/24
		dioxide or SiO or SiO?sub.2)		13:19
-	3043	((sacrifice or sacrificial) with (oxide	USPAT	2003/09/24
		or dioxide or SiO or SiO?sub.2)) and		13:19
		semiconductor		
-	8	(\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	USPAT	2003/09/24
		or dioxide or SiO or SiO?sub.2)) and		13:20
		(re\$1claim or re\$1claiming or re\$1claimed		
		or re\$1claimation)		
_	144	(re\$1claim or re\$1claiming or re\$1claimed	USPAT	2003/09/24
		or re\$1claimation) near4 (substrate or		13:21
		wafer)		
-	134	((re\$1claim or re\$1claiming or	USPAT	2003/09/24
	-	re\$1claimed or re\$1claimation) near4		15:06
		(substrate or wafer)) and @ay<=2000		
-	1	6451696.pn.	USPAT	2003/09/24
				15:24
_	4	("3715842" "3923567" "5622875"	USPAT	2003/09/24
		"5855735").PN.		15:07
-	237523	transistor	USPAT	2003/09/24
				15:24
-	168	transistor and (reclaim or reclaiming)	USPAT	2003/09/24
				15:24